Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	968793	catalyst or catalytic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:46
L2	138941	tft or thin adj5 transistor or electro$1optical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L3	1407884	laser or uv or ultra$1violet or infra$1red	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L4	1418433	crystal$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L5	1597757	amorphous adj3 (si or silicon) or a$1si or a$1silicon or semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L6	500495	irradiat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L7	1493411	oxygen or "o.sub.2" or "o2" or oxidi$5 or oxidat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L8	7692	L6 with L3 with L7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39

L9	105010	L4 near10 L5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L10	625	L8 and L9 and L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L11	20865	ldd or light adj5 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L12	997855	gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L13	3246949	source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L14	250	L10 and L12 and L13 and L11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
L15	2104	1 with promot$4 with 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:47
L16	85	14 and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:25

L17	8	(("5854096") or ("5923966") or ("6063654")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 14:28
S1	20	(("5,861,656") or ("5,471,330") or ("6,147,667") or ("5,767,531") or ("6,246,070") or ("5,763,301") or ("5,818,067") or ("6,147,667") or ("5,403,762") or ("5,342,545") or ("5,471,330") or ("6,737,717") or ("6,359,320")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 15:37
S2	138941	tft or thin adj5 transistor or electro$1optical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:13
S3	1407884	laser or uv or ultra$1violet or infra$1red	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:42
S4	1418433	crystal$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:44
S5	67599	S3 with S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:10
S6	1597757	amorphous adj3 (si or silicon) or a$1si or a$1silicon or semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:47
S7	500495	irradiat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:47

S8	192634	S7 with S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:51
S9	118735	S4 with S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:49
S10	4817	S8 and S9 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:49
S11	1493411	oxygen or "o.sub.2" or "o2" or oxidi$5 or oxidat$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:50
S12	7692	S7 with S3 with S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:52
S13	105010	S4 near10 S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:53
S14	625	S12 and S13 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:54
S15	20865	ldd or light adj5 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:54

S16	997855	gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:14
S17	3246949	source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/06 15:55
S18	250	S14 and S16 and S17 and S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:39
S19	2224	(438/151 or 438/157 or 438/166 or 438/486).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:09
S20	1407884	laser or uv or ultra$1violet or infra$1red	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:10
S21	1418433	crystal$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:10
S22	67599	S20 with S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:12
S23	1091	S19 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:12

S24	138941	tft or thin adj5 transistor or electro$1optical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:13
S25	1028	S23 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:13
S26	140134	gate adj5 (insulat$4 or dielectric or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:15
S27	904	S25 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:16